
2SA1374

Silicon PNP Epitaxial

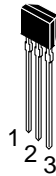
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Application

Low frequency amplifier

Outline

SPAK



- 1. Emitter
- 2. Collector
- 3. Base

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	−55	V
Collector to emitter voltage	V _{CEO}	−55	V
Emitter to base voltage	V _{EBO}	−5	V
Collector current	I _C	−100	mA
Base current	I _B	−30	mA
Collector power dissipation	P _C	300	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−55 to +150	°C

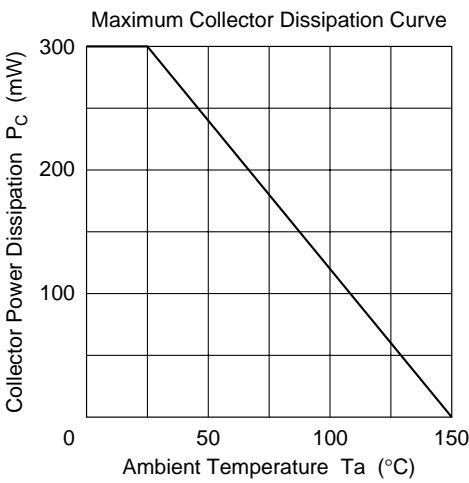
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	−55	—	—	V	I _C = −10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	−55	—	—	V	I _C = −1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	−5	—	—	V	I _E = −10 μA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	−0.1	μA	V _{CB} = −18 V, I _E = 0
Emitter cutoff current	I _{EBO}	—	—	−0.05	μA	V _{EB} = −2 V, I _E = 0
DC current transfer ratio	h _{FE} ^{*1}	160	—	500		V _{CE} = −12 V, I _C = −2 mA
Base to emitter voltage	V _{BE}	—	−0.66	−0.75	V	V _{CE} = −12 V, I _C = −2 mA
Collector to emitter saturation voltage	V _{CE(sat)}	—	−0.1	−0.5	V	I _C = −10 mA, I _B = −1 mA
Gain bandwidth product	f _T	—	250	—	MHz	V _{CE} = −12 V, I _C = −2 mA
Collector output capacitance	Cob	—	2.5	—	pF	V _{CB} = −10 V, I _E = 0, f = 1 MHz

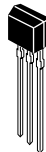
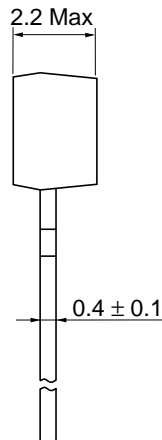
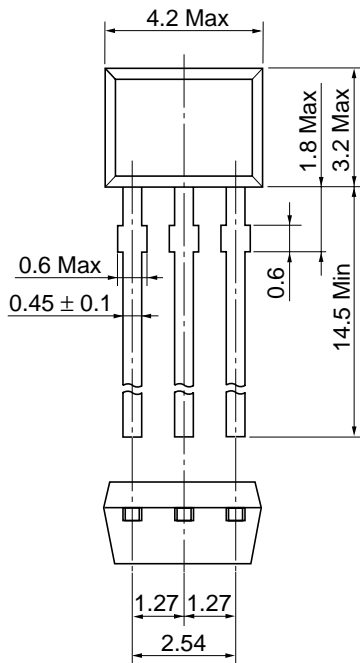
Note: 1. The 2SA1374 is grouped by h_{FE} as follows.

C	D
160 to 320	250 to 500

See characteristic curves of 2SA836.



Unit: mm



Hitachi Code	SPAK
JEDEC	—
EIAJ	—
Weight (reference value)	0.10 g

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